

SILICON TRANSISTOR 2SA1413-Z

PNP SILICON TRIPLE DIFFUSED TRANSISTOR MP-3

DESCRIPTION

2SA1413-Z is designed for High Voltage Switching, especially in Hybrid Integrated Circuits.

FEATURES

High Voltage : VcEo = −600 V

• High Speed : $t_f \le 1.0 \mu s$

• Complement to 2SC3632-Z

QUALITY GRADE

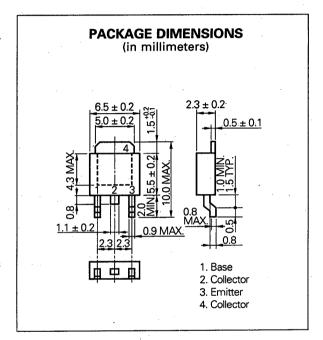
Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Collector to Base Voltage	Vсво	-600	٧
Collector to Emitter Voltage	VCEO	-600	٧
Emitter to Base Voltage	VEBO	- 7	٧
Collector Current (DC)	Ic	-1.0	Α
Collector Current (Pulse)*	lc	-2.0	Α
Total Power Dissipation (Ta = 25 °C)**	PT	2.0	W
Junction Temperature	T_j	150	°C
Storage Temperature	T _{stg} -55	to +150	°C

- * PW ≦ 10 ms, Duty Cycle ≦ 50 %
- ** When mounted on ceramic substrate of 7.5 cm² × 0.7 mm



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

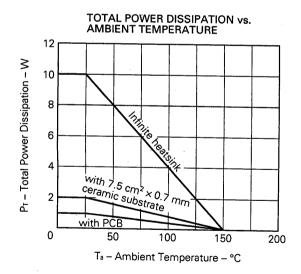
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	Ісво			-10	μΑ	VcB = -600 V, IE = 0
Emitter Cutoff Current	lebo			-10	μΑ	VEB = -7.0 V, Ic = 0
DC Current Gain	hFE1***	30	58	120		Vce = -5.0 V, Ic = -0.1 A
DC Current Gain	hFE2***	5	19			Vce = -5.0 V, Ic = -0.5 A
Collector Saturation Voltage	VCE(sat)***		-0.28	-1.0	V	Ic = -0.3 A, I _B = -60 mA
Base Saturation Voltage	V _{BE(sat)} ***		-0.85	-1.2	V	Ic = -0.3 A, Is = -60 mA
Gain Bandwidth Product	fr		28		MHz	Vce = -10 V, le = 50 mA
Output Capacitance	Соь		42		pF	Vcв = -10 V, le = 0, f = 1.0 МН;
Turn-on Time	ton		0.1	0.5	μs	Ic = -0.5 A, R _L = 500 Ω
Storage Time	tstg		3.5	5.0	μs	I _{B1} = -I _{B2} = -0.1 A
Fall time	tr		0.08	0.5	μs	Vcc = -250 V

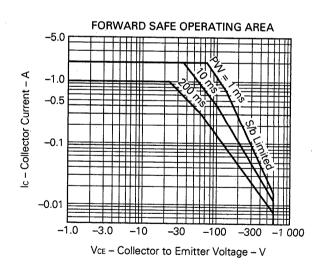
^{***} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

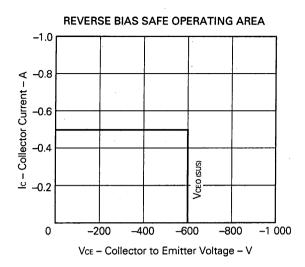
hre Classification

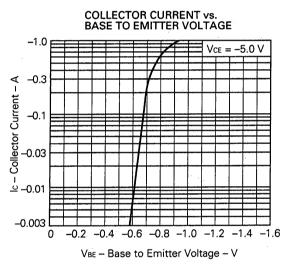
MARKING	М	L	К
hFE1	30 to 60	40 to 80	60 to 120

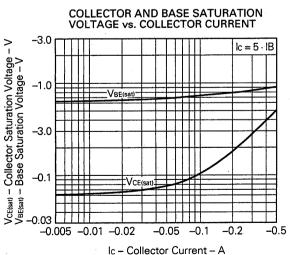
TYPICAL CHARACTERISTICS (Ta = 25 °C)

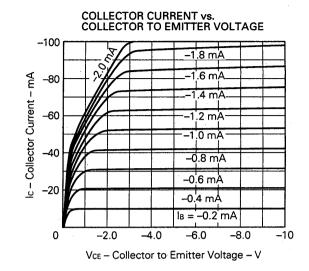


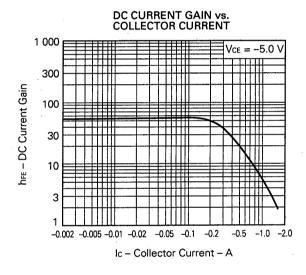


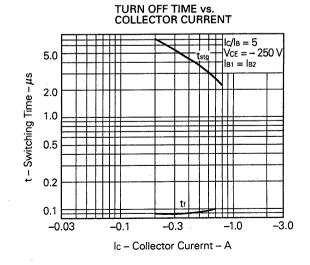


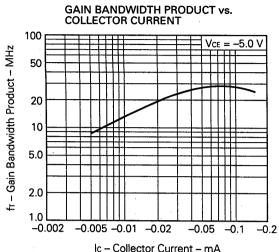


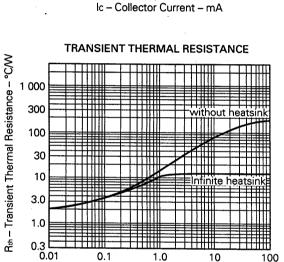




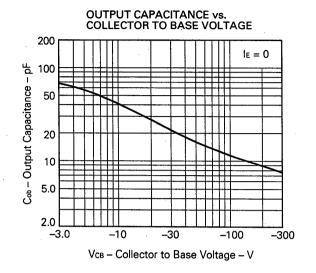








PW - Pulse Width - s



[MEMO]

Reference

Application note name	No.
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207
Design of Push-Pull Type Switching Regulators (Basic).	TEB-1002
Design of Push-Pull Type Switching Regulators (Applications).	TEB-1003
Optimum Base Drive Conditions of Switching Power Transistors.	TEB-1014

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Application examples recommended by NEC Corporation.

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime

systems, etc.